

20V P-Channel MOSFETs

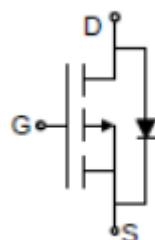
MOSFET Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}\text{Max.}$ | I_D |
|---------------|-------------------------|-------|
| -20V | 20.8mΩ@-4.5V | -8A |

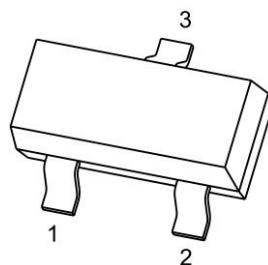
FEATURES

TrenchFET Power MOSFET

P-CHANNEL MOSFET



SOT-23



APPLICATIONS

PWM Applications
Load Switch Power Management

Maximum ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|--|-----------|------------|------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | |
| Continuous Drain Current | I_D | -8 | A |
| Pulsed Drain Current | I_{DM} | -32 | |
| Maximum Continuous Drain to Source Diode Forward | I_S | -4 | |
| Maximum Power Dissipation | P_D | 1.2 | W |
| Junction Temperature | T_J | 150 | °C/W |
| Storage Temperature | T_{stg} | -55 ~ +150 | |

MOSFET ELECTRICAL CHARACTERISTICS $T_c=25^\circ\text{C}$ unless otherwise specified

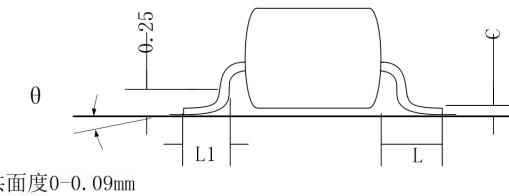
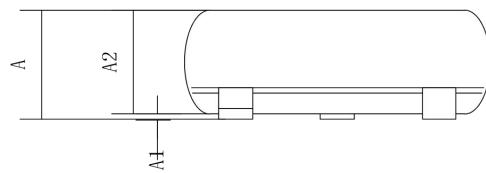
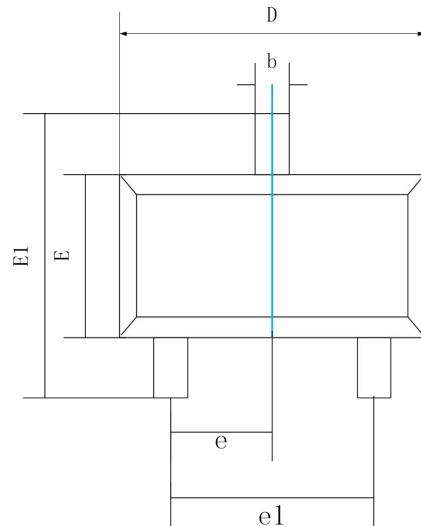
| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|---|-----------------------------|---|------|-------|-----------|------------------|
| Static | | | | | | |
| Drain-source breakdown voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$ | -20 | | | V |
| Gate-source threshold voltage | $V_{\text{GS}(\text{th})}$ | $V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$ | -0.4 | -0.68 | -1.0 | |
| Gate-source leakage | I_{GSS} | $V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 12\text{V}$ | | | ± 100 | nA |
| Zero gate voltage drain current | I_{DSS} | $V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V}$ | | | -1 | μA |
| Drain-source on-state resistance ^a | $R_{\text{DS}(\text{on})}$ | $V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -8\text{A}$ | | 17 | 20.8 | $\text{m}\Omega$ |
| | | $V_{\text{GS}} = -2.5\text{V}, I_{\text{D}} = -5\text{A}$ | | 22 | 26 | |
| Body diode voltage | V_{SD} | $I_{\text{S}} = -4\text{A}$ | | | -1.2 | V |
| Dynamic^b | | | | | | |
| Input capacitance | C_{iss} | $V_{\text{DS}} = -10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$ | | 1030 | | pF |
| Output capacitance | C_{oss} | | | 180 | | |
| Reverse transfer capacitance | C_{rss} | | | 130 | | |
| Total gate charge | Q_g | $V_{\text{DS}} = -10\text{V}, V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -5\text{A}$ | | 13 | | nC |
| Gate-source charge | Q_{gs} | | | 1.5 | | |
| Gate-drain charge | Q_{gd} | | | 3.6 | | |
| Turn-on delay time | $t_{\text{d(on)}}$ | $V_{\text{DS}} = -10\text{V}, V_{\text{GS}} = -4.5\text{A}, R_{\text{L}} = 2\Omega, R_{\text{GEN}} = 3\Omega$ | | 12 | | ns |
| Rise time | t_r | | | 10 | | |
| Turn-off delay time | $t_{\text{d(off)}}$ | | | 19 | | |
| Fall time | t_f | | | 25 | | |

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Package Mechanical Data

SOT-23



| Symbol | Dimensions In Millimeters | |
|----------|---------------------------|------|
| | Min. | Max. |
| A | 0.90 | 1.15 |
| A1 | 0.00 | 0.10 |
| A2 | 0.90 | 1.05 |
| b | 0.30 | 0.50 |
| c | 0.08 | 0.15 |
| D | 2.80 | 3.00 |
| E | 1.20 | 1.40 |
| E1 | 2.25 | 2.55 |
| e | 0.95 REF. | |
| e1 | 1.80 | 2.00 |
| L | 0.55 REF. | |
| L1 | 0.30 | 0.50 |
| θ | 0° | 8° |

V 1.1